### TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT SILICON MONOLITHIC

# **TA8053H**

### 3A DC MOTOR DRIVER WITH DIAGNOSIS

The TA8053H is a bidirectional DC motor driver with a current capacity of 3A. Inputs DI1 and DI2 are combined to select one of forward, reverse, stop, and brake modes.

The inputs are TTL-compatible, and separate power supplies are provided for the logic and output sections. The IC also incorporates various protective functions as well as a self-diagnostic function for diagnostic output

# **FEATURES**

Output current capacity : 3A (Max.)
 Small standby current consumption : 100µA (Max.)

• Four operation modes : Forward, reverse, stop,

and brake

• Multiple protective functions : Short-circuit protection, thermal shutdown, and over-voltage shutdown

Self-diagnostic output
 On short-circuit detection

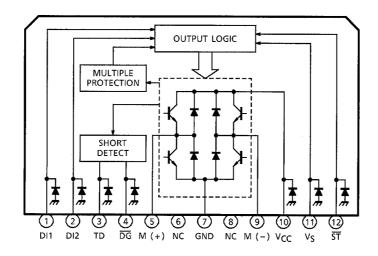
Built-in counter electromotive force absorption diodes.

• Plastic package HZIP-12pin

# HZIP12-P-1.78B

Weight: 4.0 g (Typ.)

### **BLOCK DIAGRAM AND PIN LAYOUT**



# **PIN DESCRIPTION**

PIN No.	SYMBOL	DESCRIPTION			
1 2	DI1 DI2	Output status control pin. Connects to a PNP-type voltage comparator.			
3	TD	Delays the $\overline{DG}$ output. A capacitor is placed between this pin and GND.When the pin is open, $\overline{DG}$ is in switching state.			
4	DG	Self-diagnostic output pin. When the output current increases above 6A (typically), a switching waveform is output from this pin as from M (+) and M (–). If a capacitor is connected to the TD pin, the signal from this pin will go low after a certain delay. The output is an open-collector output. The delay time is approximately calculated by the following formula : $T_D \text{ (ms)} = 50 \times C_T \text{ (}\mu\text{F)} \\ \text{Permissible } C_T \text{ range} : 0.01 \mu\text{F to } 2\mu\text{F}$			
5	M (+)	Connects to the DC motor. Both the sink and the source have a current capacity of 3A. Diodes for absorbing counter electromotive force are contained on the V <sub>CC</sub> and GND sides.			
7	GND	Grounded			
9	M (-)	Connects to the DC motor together with pin 5 and has the same function as pin 5. This pin is controlled by the inputs from pins 1 and 2.			
10	V <sub>CC</sub>	Power supply pin for the output section			
11	Vs	Power supply pin for the control section. This pin is completely separated from the V <sub>CC</sub> pin.			
12	ST	When this pin is opened or grounded, the output turns off to reduce the current consumption below 100 $\mu$ A. If standby mode is not needed, the pin is connected to V <sub>CC</sub> .			
6, 8	NC	Not connected. (Electrically, this pin is completely open.)			

# **TRUTH TABLE**

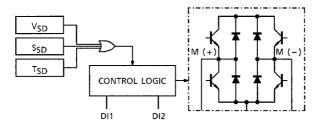
INPUT			OUTPUT	OUTDUT MODE		
DI1	DI2	ST	M (+)	M (-)	OUTPUT MODE	
Н	Н	Н	L	L	BRAKE	
L	Н	Н	L	Н	REVERSE	
Н	L	Н	Н	L	FORWARD	
L	L	Н	OFF (high impedance)		STOP	
H/L	H/L	L	OFF (high i	mpedance)	STANDBY	

### **DESCRIPTION OF MULTI-PROTECTIVE OPERATION**

The TA8053H has functions for protection from over-voltage (VSD), over-current (ISD), and overheat (TSD). These functions protect the IC (and the motor load in some cases) from deterioration or destruction due to power-related overstress.

The three functions work independently.

Each function is explained below.



### 1. Overvoltage protection (V<sub>SD</sub>)

### · Basic operation

When the voltage supplied to the  $V_{\rm CC}$  pin is up to the  $V_{\rm SD}$  detection voltage, the output is controlled by the input signals. However, when the  $V_{\rm CC}$  voltage exceeds the detection voltage, the output enters high-impedance state regardless of the input signals.

### · Detailed explanation

The V<sub>SD</sub> voltage is detected by comparing the reference voltage which is constructed by zenner diode. When the center voltage of the resistor is higher than the Zener voltage, a transistor-off instruction is issued to the control logic. When it is lower than the Zener voltage, the logic is controlled by the input signals from pins 1 and 2.

### 2. Overheat protection (T<sub>SD</sub>)

### Basic operation

When the junction (chip) temperature is up to the TSD detection temperature, the output is controlled by the input signals. When it exceeds the TSD detection temperature, the output enters high-impedance state regardless of the input signals.

### · Detailed explanation

The temperature is detected by monitoring VBE of a transistor on the chip. When the transistor VBE is lower than the internal reference voltage, an output transistor-off instruction is issued to the control logic. When it is higher than the internal reference voltage, the logic is controlled by the input signals from pins 1 and 2.

3

### 3. Overcurrent protections (ISD)

### Basic operation

When the output current (pin 5 or 9, I sink or I source) is up to the ISD detection current, the output is controlled by the input signals. When it exceeds the detection current, the output assumes a switching waveform as shown in Fig.1.

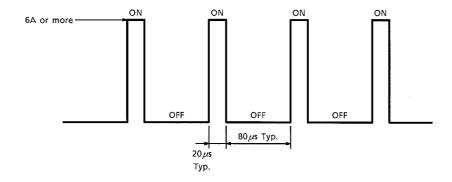


Fig.1 Basic Operation

4

### · Detailed explanation

The output current is detected by monitoring the VBE from each output transistor. One detection circuit connects to one of the output transistors and leads to the short-circuit protection circuit. When a current exceeding the ISD detection current flows through one of the four output transistors, the short-circuit protection circuit is activated. This circuit contains a timer. When over-current condition continues for 20µs (typically), the protection circuit places the output in high-impedance mode and, 80µs (typically) later, returns the IC to ON mode. The switching-waveform output is repeated until over-current condition is no longer present.

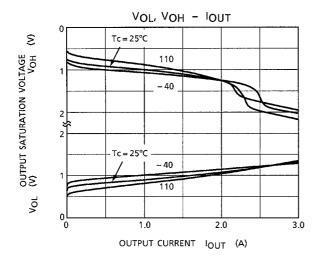
## MAXIMUM RATINGS (Ta = 25°C)

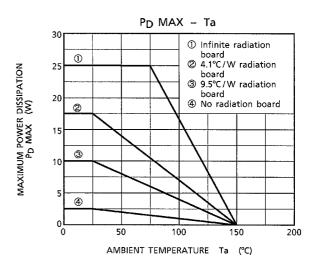
CHARACTERISTIC	SYMBOL	RATING	UNIT		
Power Supply Voltage	V <sub>CC</sub>	30	V		
Fower Supply Voltage	$V_{CC}$	60 (1s)	] '		
Input Voltage	V <sub>IN</sub>	-0.3~V <sub>CC</sub>	V		
Output Current	I <sub>O AVE</sub>	3.0	Α		
Operation Temperature	T <sub>opr</sub>	-40~110	°C		
Storage Temperature	T <sub>stg</sub>	-55~150	°C		
Power Dissipation	$P_{D}$	25	W		
Lead Temperature Time	T <sub>sol</sub>	260 (10s)	°C		

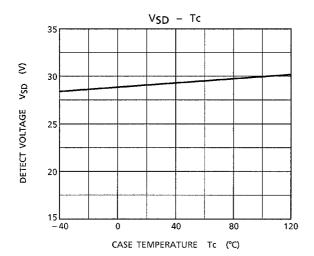
# ELECTRICAL CHARACTERISTICS ( $V_{CC} = 6\sim16V$ , $T_{C} = -40\sim110^{\circ}C$ )

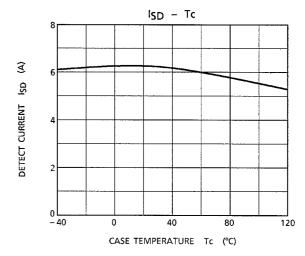
CHARACTERISTIC	SYMBOL	PIN	TEST CIR- CUIT	TEST CONDITION	MIN	TYP.	MAX	UNIT	
	I <sub>S1</sub>	Vs	_	Stop	_	8	14	mA	
Current Consumption (I)	I <sub>S2</sub>		_	Forward / Reverse	_	22	42		
	I <sub>S3</sub>		_	Brake	_	22	42		
	I <sub>CC1</sub>	V <sub>CC</sub>	_	Stop	_	5	8	mA	
Current Consumption (II)	I <sub>CC2</sub>		_	Forward / Reverse	_	18	42		
	I <sub>CC3</sub>		_	Brake	_	5	8		
Input Voltage	V <sub>IL</sub>	DI1 / DI2	_	_	_	_	0.8	V	
input voltage	V <sub>IH</sub>	טווו טוב	_	_	2.0	_	_		
Input Current	I <sub>IL</sub>	DI1 / DI2	_	V <sub>IN</sub> = 0.4	_	_	-50	- μΑ	
input Guirent	I <sub>IH</sub>	DITTDIZ	_	V <sub>IN</sub> = V <sub>CC</sub>	_	_	10		
Input Voltago	V <sub>IL</sub>	ST	_	_	_	_	0.8	V	
Input Voltage	V <sub>IH</sub>		_	_	2.0	_	_		
Input Current	I <sub>IL</sub>	ST	_	V <sub>IN</sub> = 0.4	_	_	50	μA	
input Guirent	I <sub>IH</sub>		_	V <sub>IN</sub> = V <sub>CC</sub>	_	_	4	mA	
Output Saturation Voltage	V <sub>sat</sub> (total)	M (+) / M (-)	_	I <sub>O</sub> = 1.5A	1.0	2.1	2.8	V	
Output Saturation Voltage	V <sub>Sat</sub> (lolal)		_	I <sub>O</sub> = 3.0A	2.0	3.3	4.1		
Output Leakage Current	I <sub>LEAK-U</sub>	M (+) /	_	V <sub>O</sub> = 0V	_	_	-100	μΑ	
Output Leakage Current	I <sub>LEAK-L</sub>	M (-)	_	V <sub>O</sub> = V <sub>CC</sub>	_	_	100		
Output Voltage	V <sub>OL</sub>	DL DG	_	I <sub>OL</sub> = 3mA	_	_	0.5	V	
Output Leakage Current	I <sub>LEAK-L</sub>	DG	_	V <sub>OUT</sub> = V <sub>CC</sub>	_	_	10	μA	
Diode Forward Voltage	V <sub>F-U</sub>	M (+) / M (-)	_	I <sub>F</sub> = 3.0A	_	5.0	_	V	
Diode Forward Voltage	V <sub>F-L</sub>		_	I <sub>F</sub> = 3.0A	_	1.5	_		
Overcurrent Detection	I <sub>SD</sub>	_	_	_	4.2	6	8	Α	
Shutdown Temperature	T <sub>SD</sub>	_	_	_	_	150	_	°C	
Overvoltage Detection	V <sub>SD</sub>	_	_	_	26	29	32	V	
Standby Current	IS	V <sub>CC</sub> +V <sub>S</sub>	_	ST = GND	_	_	100	μA	
Thermal Resistance	Rθ <sub>j-c</sub>	_	_	_	_	3	_	°C/W	
Transfer Delay Time	t <sub>pLH</sub>	_	_	_	_	1	10		
Transfer Delay Time	t <sub>pHL</sub>	_	_	_		1	10	μs	

5 2002-01-30

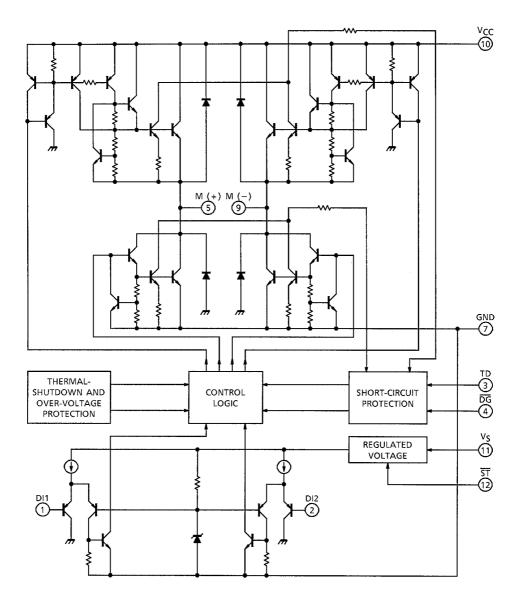






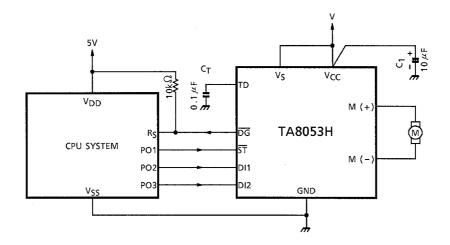


# I/O EQUIVALENT CIRCUIT



2002-01-30

# **EXAMPLE OF APPLICATION CIRCUIT**



(\*): Cautions for wiring

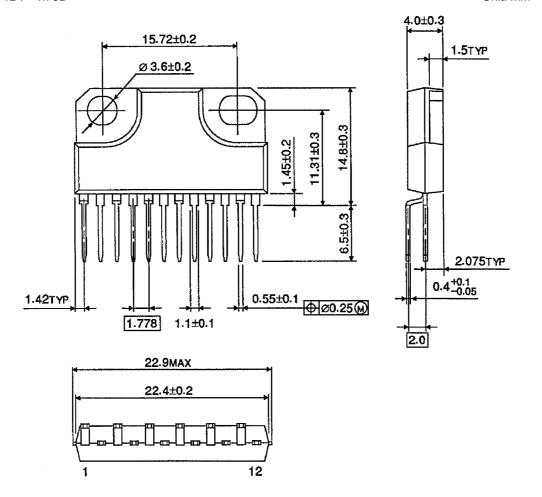
 $\ensuremath{C_1}$  is for absorbing disturbance noise, etc.

So, connect it as close as possible.

# **Package Dimensions**

HZIP12-P- 1.78B

Unit: mm



9

Weight: 4.0 g (Typ.)

2002-01-30

# **RESTRICTIONS ON PRODUCT USE**

000707EAA\_S

- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The information contained herein is presented only as a guide for the applications of our products. No
  responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other
  rights of the third parties which may result from its use. No license is granted by implication or otherwise under
  any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.